

INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

Docket Number (Optional)

FIS92000039

Application Number

Applicant(s)

KHARE ET AL.

Filing Date

Group Art Unit

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
BJ		5,578,848	11/26/1996	Kwong et al.	257	296	
BJ		5,674,788	10/7/1997	Wristers et al.	437	239	
BJ		5,861,651	1/19/1999	Brasen et al.	438	253	
BJ		5,880,040	3/9/1999	Sun et al.	257	411	
BJ		6,017,791	1/25/2000	Wang et al.	438	253	
BJ		6,087,236	7/11/2000	Chau et al.	438	301	
BJ		6,110,842	8/29/2000	Okuno et al.	438	746	
BJ		6,140,024	10/31/2000	Misium et al.	430	314	

FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

BJ		Lucovsky, G., "Ultrathin Nitrided Gate Dielectrics: Plasma Processing, Chemical Characterization, Performance and Reliability," IBM JOURNAL OF RESEARCH & DEVELOPMENT, Vol. 43, No. 3, 1999, pages 1 - 27
BJ		Gusev, E.P.; Lu, H.C.; Garfunkel, E. L.; Gustafsson, T.; and Green, M. L., "Growth and Characterization of Ultrathin Nitrided Silicon Oxide Film," IBM JOURNAL OF RESEARCH AND DEVELOPMENT, Vol. 43, No. 3, 1999, pages 1-22.

EXAMINER

Fernando Toledo

DATE CONSIDERED

February 19, 2002

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.